

Homework #5 Solutions

EE482
Fall '02

2. (a) $N_d \gg N_a$, so diode current is primarily electrons injected into p-side $J \approx J_{np}$ (ignoring recomb. in depletion region)

$$J = 100 \frac{\text{A}}{\text{cm}^2} = J_{np} = \frac{Q_n}{\tau_n} \quad Q_n = 100 \frac{\text{A}}{\text{cm}^2} (10^{-6} \text{s}) = 10^{-4} \text{C/cm}^2$$

(b) $Q_d = \sqrt{2K_s \epsilon_0 q N_a (\phi_i - V_a)}$ $D_n \approx 21 \frac{\text{cm}^2}{\text{s}}$

$$J_{np} = q \frac{n_i^2}{N_a} \left(\frac{D_n}{L_n} \right) \exp\left(\frac{qV_a}{kT}\right) \quad L_n = (D_n \tau_n)^{1/2} = 4.6 \times 10^{-3} \text{cm}$$

$$= (1.6 \times 10^{-19} \text{C}) \left(\frac{2 \times 10^{20} \text{cm}^{-6}}{10^{17} \text{cm}^{-3}} \right) \left(\frac{21 \text{cm}^2/\text{s}}{4.6 \times 10^{-3} \text{cm}} \right) \exp\left(\frac{qV_a}{kT}\right) = 46 \mu\text{m}$$

$$= 1.46 \times 10^{-12} \frac{\text{A}}{\text{cm}^2} \exp\left(\frac{qV_a}{kT}\right) = 100 \frac{\text{A}}{\text{cm}^2} \Rightarrow V_a = 0.83 \text{V}$$

Assume $E_f \approx E_c$ on n-side, so $\phi_i = \frac{kT}{q} \ln\left(\frac{(3 \times 10^{19})(10^{17})}{2 \times 10^{20}}\right)$

$$Q_d = \begin{cases} 1.79 \times 10^{-7} \frac{\text{C}}{\text{cm}^2} & V_a = 0 \\ 0.66 \times 10^{-7} \frac{\text{C}}{\text{cm}^2} & V_a = 0.83 \text{V} \quad (\phi_i - V_a) = 0.13 \text{V} \end{cases} = 0.96 \text{V}$$

(c) Divide switching into two parts:

As V_{diode} rises from 0, first only depletion charge is changing significantly, then at end Q_n increases exponentially with V_{diode} . Also, until Q_n rises to within

$$\Delta t_1 = \frac{\Delta Q_d}{I_{\text{avg}}} = \frac{1.13 \times 10^{-7} \text{C/cm}^2}{100 \text{A/cm}^2} = 1.13 \times 10^{-9} \text{s} = 1.13 \text{ns}$$

a few kT of final value, very little current is required to compensate for recombination of injected minority carriers ($\frac{Q_n}{\tau_n}$)

For second stage Q_n and thus $\frac{Q_n}{\tau_n}$ becomes significant
 Can neglect ΔQ_{depl} since ΔV is small and we have
 already accounted for it in full.

$$I_f = \frac{Q_n}{\tau_n} + \frac{dQ_n}{dt}$$

$$Q_n = I_f \tau_n \left[1 - \exp\left(-\frac{t}{\tau_n}\right) \right]$$

$$= 10^{-4} \frac{\text{C}}{\text{cm}^2} \left[1 - \exp\left(-\frac{t}{\tau_n}\right) \right]$$

(i) 63% of final value: $\left[1 - \exp\left(-\frac{t_2}{\tau_n}\right) \right] = 0.63$

$$\Delta t_2 = \tau_n = 10^{-6} \text{ s}$$

$$t_{\text{turn-on}} = \Delta t_1 + \Delta t_2 = 1.3 \times 10^{-9} \text{ s} + 10^{-6} \text{ s} = 10^{-6} \text{ s}$$

(ii) $V_a = 0.83 - 0.1 = 0.73 \text{ V}$ $Q_n = 10^{-4} \frac{\text{C}}{\text{cm}^2} \exp\left(-\frac{0.1 \text{ V}}{0.026 \text{ V}}\right)$

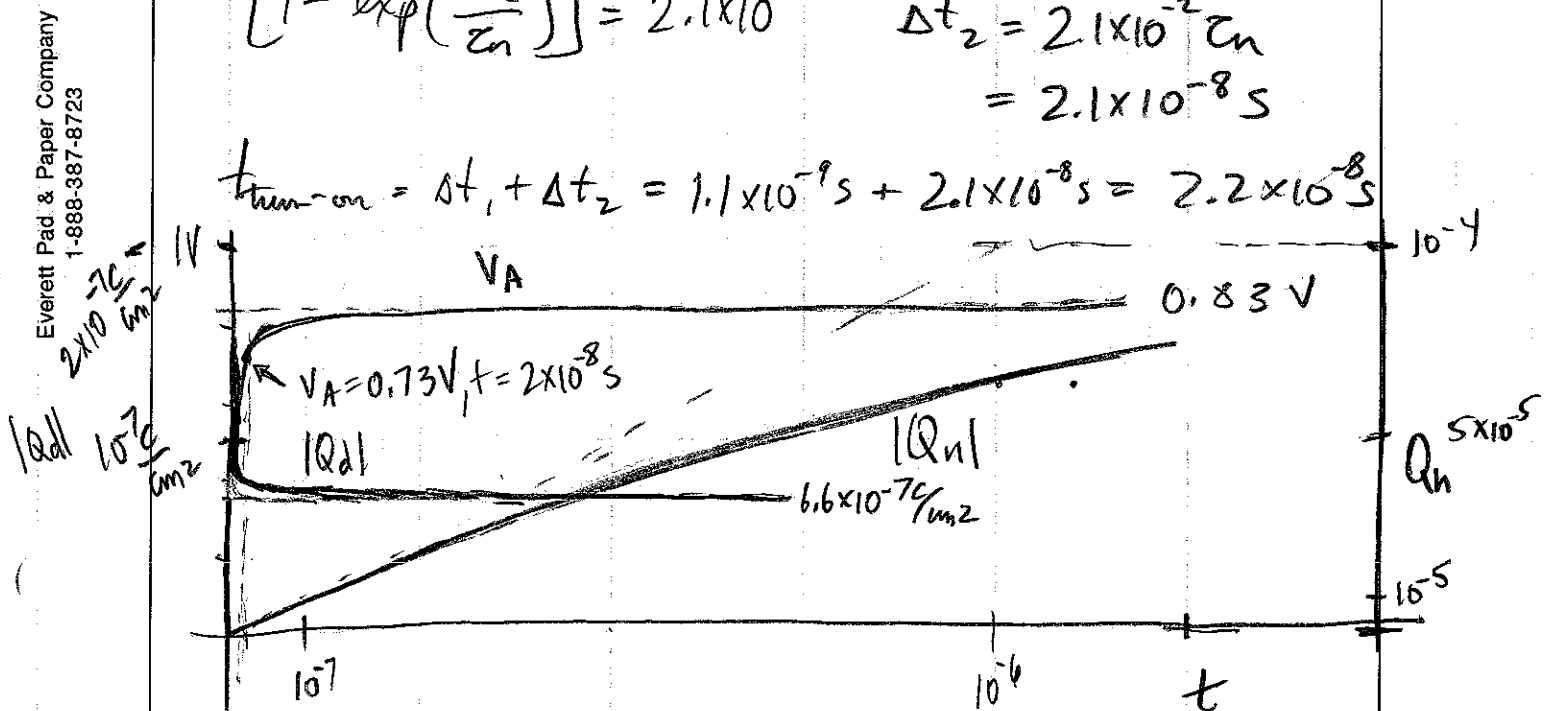
$$= 2.1 \times 10^{-6} \text{ C/cm}^2$$

$$\left[1 - \exp\left(-\frac{\Delta t_2}{\tau_n}\right) \right] = 2.1 \times 10^{-2}$$

$$\Delta t_2 = 2.1 \times 10^{-2} \tau_n$$

$$= 2.1 \times 10^{-8} \text{ s}$$

$$t_{\text{turn-on}} = \Delta t_1 + \Delta t_2 = 1.1 \times 10^{-9} \text{ s} + 2.1 \times 10^{-8} \text{ s} = 2.2 \times 10^{-8} \text{ s}$$



(d) Storage time

$$I_R = \frac{Q_n}{\tau_n} + \frac{dQ_n}{dt} = -100 \frac{A}{cm^2}$$

$$Q_n(t=0) = I_f \tau_n = 10^{-4} \frac{C}{cm^2}$$

$$Q_n = A + B e^{-t/\tau_n}$$

$$A + B = Q_n(t=0) = 10^{-4} \frac{C}{cm^2}$$

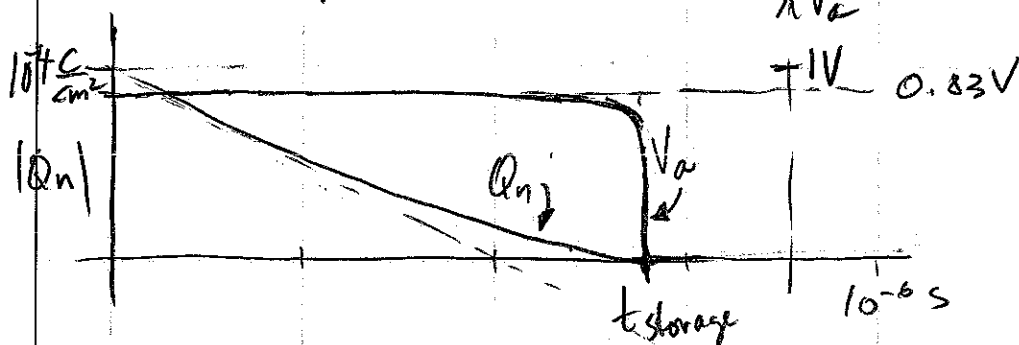
$$= 10^{-4} \frac{C}{cm^2} (2e^{-t/\tau_n} - 1)$$

$$A = I_R \tau_n = -10^{-4} \frac{C}{cm^2}$$

$t_{storage}$ defined for $Q_n = 0$

$$2e^{-t/\tau_n} = 1$$

$$t_{storage} = 6.9 \times 10^{-7} s$$



(e) For short base,

$$J_{np} = \frac{q n_i^2}{N_a} \left(\frac{D_n}{W_p} \right) \left[\exp\left(\frac{q V_a}{kT}\right) - 1 \right]$$

$$Q_n = \frac{1}{2} W_p \frac{q n_i^2}{N_a} \left[\exp\left(\frac{q V_a}{kT}\right) - 1 \right]$$

$$= J_{np} \left(\frac{W_p^2}{2 D_n \tau_n} \right) = J_{np} (6 \times 10^{-11} s)$$

transit time: average time for minority carriers to cross neutral region, which is average lifetime due to fast recomb. at contact

$$Q_n = 6 \times 10^{-9} \frac{C}{cm^2} \quad V_a = 0.71 V$$

$$Q_{deple}(0.71V) = 0.91 \times 10^{-7} C/cm^2$$

ΔQ MUCH smaller, switching MUCH faster.